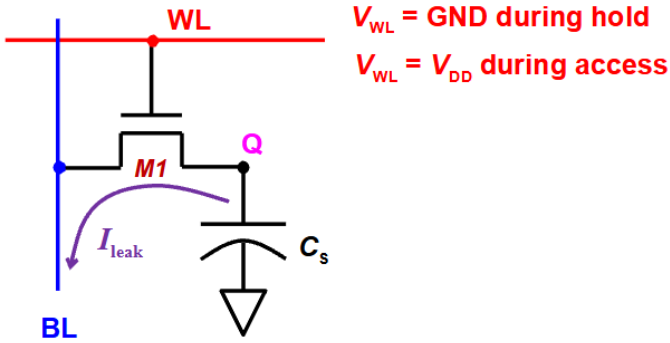


# DRAM Analysis

## 1 DRAM operation



Operation of DRAM is as follows ...

- Bitcell is *accessed* to read or write data into the bitcell
  - Electrically connect BL to *storage node* Q
- Otherwise, bitcell is in *hold* mode and retains stored data
  - Affected by leakage current  $I_{leak}$
  - Larger  $C_s$  allows for more charge to be stored (and higher data retention time before refresh is required)

Figure 1: DRAM Bitcell

### 1.1 DRAM Write

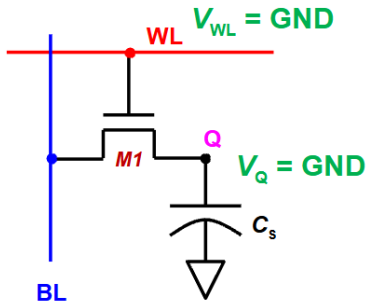


Figure 2: Initial state  
 WL is off, capacitor charge is zero

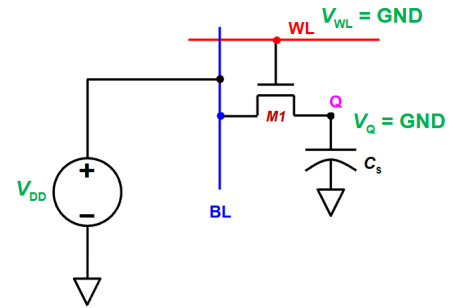


Figure 3: Suppose we want to write 1  
 Precharge BL to  $V_{DD}$

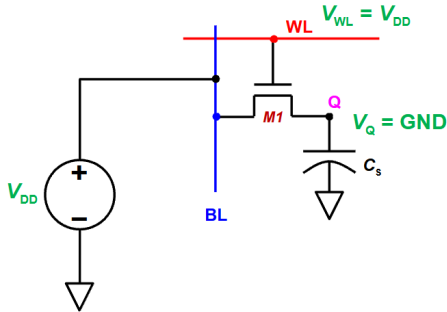


Figure 4: Turn on WL

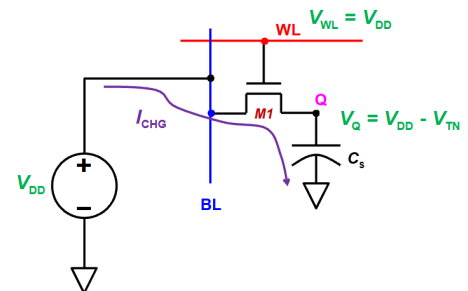


Figure 5: Current flows into  $C_s$   
 NMOS passes weak 1, therefore  $V_Q$  goes up to  $V_{DD} - V_{TH}$

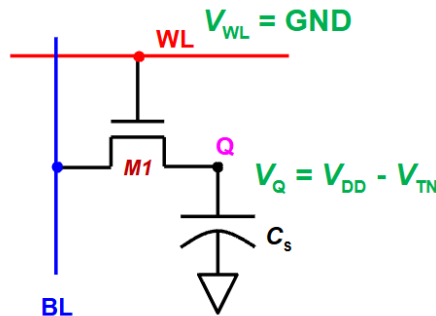


Figure 6: Data successfully written into bitcell  
 WL can be turned off, voltage at BL can be removed

## 1.2 DRAM Read

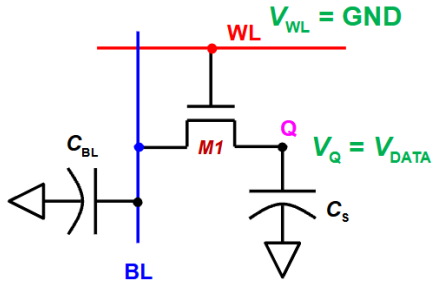


Figure 7: We want to read  $V_{DATA}$  stored on  $V_Q$   
Notice that there is parasitic  $C_{BL}$  on BL

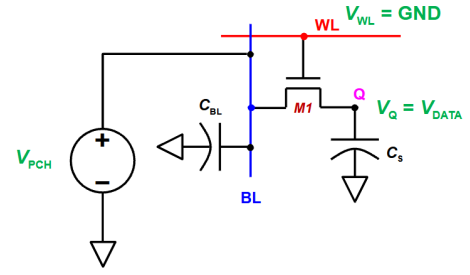


Figure 8: Precharge BL to  $V_{PCH}$   
Note that  $V_{PCH}$  may be lower than  $V_{DD}$

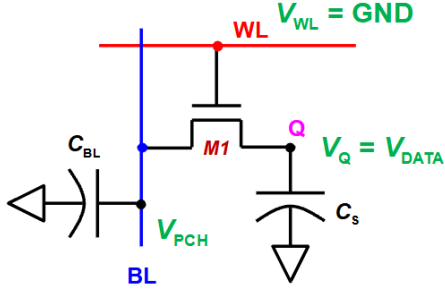


Figure 9:  $C_{BL}$  now holds onto  $V_{PCH}$   
ie. high impedance node

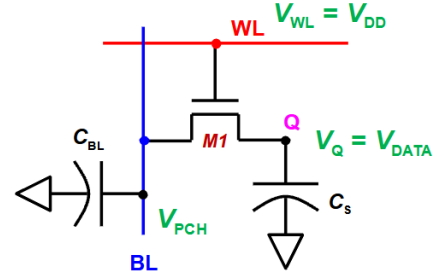


Figure 10: Turn on the WL, short-circuiting  $C_S$  with  $C_{BL}$   
Charge-sharing occurs

### 1.2.1 Charge Sharing

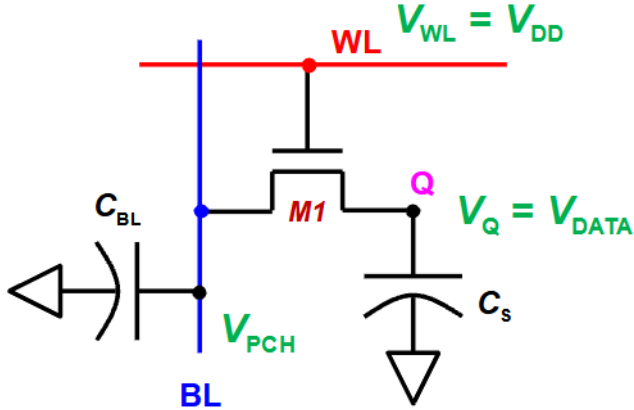


Figure 11: Charge Sharing

- $Q_S = C_S V_{DATA}$
- $Q_{BL} = C_{BL} V_{PCH}$
- $Q_{TOTAL} = Q_{BL} + Q_S$

When M1 turns on ...

- $\Delta V_{BL} = \frac{Q_{TOTAL}}{C_{BL} + C_S} - V_{PCH}$
- $\Delta V_Q = \frac{Q_{TOTAL}}{C_{BL} + C_S} - V_{DATA}$

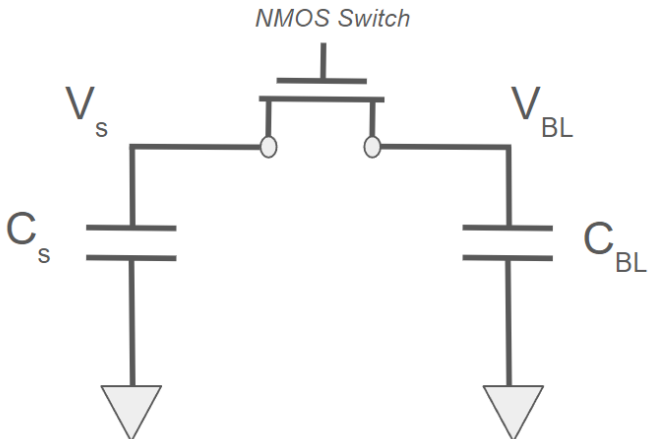


Figure 12: Charge Sharing (Alternative view)

$$\underbrace{C_S V_S + C_{BL} \frac{V_{DD}}{2}}_{\text{Initial charge; NMOS open}} = \underbrace{(C_S + C_{BL}) V_{common}}_{\text{After charge sharing; NMOS closed}}$$

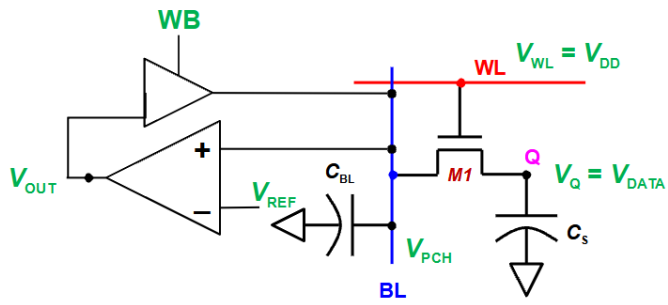
- If store 1, then  $V_S = V_{DD}$
- Assume that  $V_{BL}$  is precharged to  $\frac{V_{DD}}{2}$

We can rearrange the above equation to get ...

$$\Delta V_{BL} = V_{common} - V_{BL} = \frac{C_S}{C_S + C_{BL}} \cdot \frac{V_{DD}}{2}$$

From this, we can see that we want  $C_S \gg C_{BL}$

### 1.2.2 Sense Amplifier and Writeback



- $V_{REF}$  must be tuned correctly
- WB ensures that we rectify our destructive read

Figure 13: Op-amp with writeback